FAST HIGH VOLTAGE TRANSISTOR SWITCHES

The high-voltage switches of the model series HTS-SI and HTS-FI have been especially designed for scientific and industrial power pulse applications which require a fast and reproducible switching of peak currents at the kiloampere level. To achieve this, state-of-the-art power semiconductor devices, so-called IGBT's (Insulated Gate Bipolar Transistors) have been employed. These new switching elements of power electronics represent in principal a combination of the classical bipolar transistor with the modern vertical MOSFET. The advantages of both technologies; the current capability and low voltage drop of the bipolar transistor plus the high switching speed of the MOSFET, are ideally combined in the IGBT. By using a hundred or more interconnected IGBT's the switching modules of series HTS-SI/FI achieve the pulse power capability of gas discharge tubes and spark gaps. Additionally, IGBT switches offer advantages like simple connection, short recovery time, low jitter and last but not least the lifetime typical of semiconductor devices.

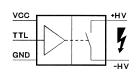
The turn-on rise times of BEHLKE IGBT switches are in practice mainly only limited by the circuit stray inductance. In contrast the turn-off rise times are determined by the bipolar characteristics of the IGBT's. Due to the recombination time of the minority carriers a relatively long turn-off-phase occurs. The turn-off-phase lasts approximately 5 μ s for the HTS-SI (- Standard IGBT) and approximately 1 μ s for the HTS-FI (- Fast IGBT) switch. The ontime corresponds to the control signal and can be varied between ton(min) and infinity. Being galvanically isolated, the devices can be used as high-side switches for positive as well as for negative voltages. The modules are protected against thermal overload, too high a signal frequency, unsuitable control signals, and incompatible auxiliary supplies. For reasons of reliability the devices are completely resinencapsulated, but in case of failure, a costeffective repair is possible at factory.

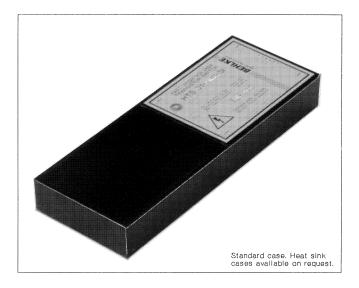
IMPORTANT!

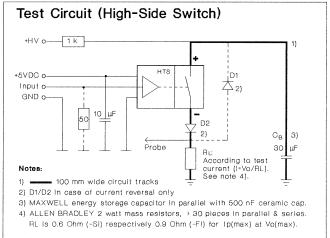
Do not exceed the rated reverse-blocking voltage, otherwise an undefined breakdown of the switch may occur. If the risk of a current reversal exists (caused by unclamped inductive loads or poor circuit layouts) the switch should be protected by an adequate external diode. For lowest stray inductances the switch should be contacted over the whole width of its terminal blocks. Mounting on a double-sided printed circuit board with 100 mm (4 inch) wide circuit tracks is recommended. In case of pulse transmission an impedance matching between switch, line and load has to be provided. For further design recommendations please refer to the general instructions.

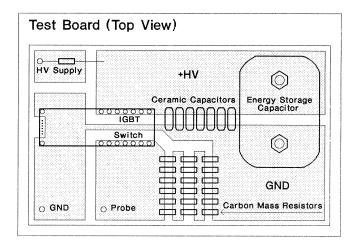
HTS 31-480-SI 3 kV, 4.8 kA HTS 31-320-FI 3 kV, 3.2 kA

- IGBT Technology
- High di/dt Capability
- Full Peak Current Turn-Off Capability











TECHNICAL DATA (Preliminary 10/93)

SPECIFICATION	SYMBOL	CONDITION / COMMENT	31-480-SI	31-320-FI	UNIT
Maximum Operating Voltage	V _{O(max)}	T _{case} = 25°C	±3000		VDC
Minimum Operating Voltage	V _{O(min)}	Recommended for saturated switching	300		VDC
Breakdown Voltage	V _{br}	$I_{off} > 10 \text{ mA}, T_{case} = 25 ^{\circ}\text{C}$	3300		VDC
Temperature Coefficient of V _{br}			+4.5	+3.78	V/°C
Max. Reverse Blocking Voltage	V _{rb}		90		VDC
Isolation Voltage		Continuously	10000		VDC
Typical Saturation Voltage	Vı	0.1 x I _{P(max)} , 0.8 x V _O , T _{case} = 25 °C	9	13	,
	V _{sat}	1.0 x I _{P(mux)} , 0.8 x V _O , T _{case} = 25°C	60	42	VDC
Maximum Peak Current 1)		$t_p < 100 \mu s$, duty cycle $< 1\%$, $T_{case} = 25 ^{\circ}C$	4800	3200	
	I _{P(max)}	t_p < 1 ms, duty cycle <1%, T_{case} = 25°C	3000	2000	
	,,	$t_p < 100 \mu s$, duty cycle 50%, $T_{case} = 25 ^{\circ}\text{C}$	1650	1100	
		t _o < 1 s, duty cycle 50%, T _{case} =25°C	1200	800	ADC
Maximum Continuous Current		Standard plastic case, T _{case} = 25 °C	6	4	ADC
Maximum Off-State Current	IL.	0.8 x V ₀ , T _{case} = 25 °C	1.5		mADC
Minimum On-Time	l _{off}		1	0.2	μs
Turn-On Delay Time	t _{on(min)}	0.1 x I _{P(max)}	130		ns
Typical Turn-On Rise Time	t _{d(on)}	0.1 x I _{P(max)} , 0.8 x V ₀	50	30	
	t _{r(on)}	1.0 x I _{P(max)} , 0.8 x V _O	200	150	ns
Typical Turn-Off Rise Time 2)		Resistive load	5	0.8	μs
Typical Turn-On Jitter	t _{r(off)}	$V_{tr} = 5VDC$, $V_{aux} = 5.00 VDC$	500		ps
Maximum Burst Frequency 1)	t _{i(on)}	(1 / Minimum Pulse Spacing)	0.25	1	MHz
Max. Number of Pulses/Burst 1)	f _{b(max)}	Use burst option for >20 pulses / 100µs	20		
Max. Continuous Frequency 1)	N _B		1	6	kHZ
Max. Cont. Power Dissipation	f _{c(max)}	Increased P _{d(max)} on request	25		Watts
Linear Temp. Derating of P _{d(max)}	P _{d(max)}	T _{case} >25°C	0.55		W/°C
Temperature Range		Extented temperature range on request	-30 + 70		°C
Switch Natural Capacitance	To	Capacitance between switch poles	1200	800	pF
Coupling Capacitance	C _N	Between power and control part	30		рF
Auxiliary Supply Voltage	C _C	Maximum tolerance ± 5%	5		VDC
Auxiliary Supply Current	V _{aux}	@ fc _(max)	400		mADC
Control Voltage	l _{aux}	>3VDC recommended	2-10		VDC
Fault Detection Signal	V _{tr}	"Low" in case of fault	High: 4.8 (Typ.)	Low: 0.2	VDC
Dimensions		Case only	199.5 x 76.4	x 25.4	mm ³
Weight			750		g

- 1) CAUTION: These data have to be considered in conjunction with the maximum continuous power dissipation! Please refer to the general instructions.
- 2) Faster turn-off rise times are optionally available at reduced peak current capability. Please consult factory.

